5.0 V Dual TTL to Differential PECL Translator

MC100ELT22

The MC100ELT22 is a dual TTL to differential PECL translator. Because PECL (Positive ECL) levels are used only +5 V and ground are required. The small outline 8-lead package and the low skew, dual gate design of the ELT22 makes it ideal for applications which require the translation of a clock and a data signal.

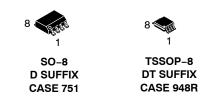
Features

- 1.2 ns Typical Propagation Delay
- < 300 ps Typical Output to Output Skew
- PNP TTL Inputs for Minimal Loading
- Flow Through Pinouts
- Operating Range: $V_{CC} = 4.75$ V to 5.25 V with GND = 0 V
- No Internal Input Pulldown Resistors
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

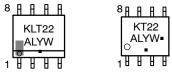


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MARKING DIAGRAMS*





- L = Wafer Lot
- Y = Year
- W = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

*For additional information, see Application Note <u>AND8002/D</u>.

ORDERING INFORMATION

Device	Package	Shipping [†]
MC100ELT22DG	SO-8 (Pb-Free)	98 Units / Tube
MC100ELT22DR2G	SO-8 (Pb-Free)	2500 Tape & Reel
MC100ELT22DTG	TSSOP-8 (Pb-Free)	100 Units / Tube
MC100ELT22DTR2G	TSSOP-8 (Pb-Free)	2500 Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

MC100ELT22

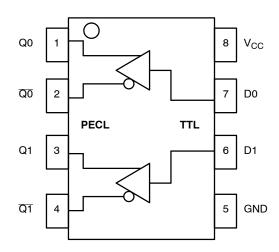


Figure 1. Logic Diagram and Pinout Assignment

Table 1. PIN DESCRIPTION

Pin	Function
Qn, Qn	PECL Differential Outputs*
Dn	TTL Inputs
V _{CC}	Positive Supply
GND	Ground

*Output state undetermined when inputs are open.

Table 2. ATTRIBUTES

Characteristics	Value
Internal Input Pulldown Resistor	N/A
Internal Input Pullup Resistor	N/A
ESD Protection Human Body Model Machine Model	> 2 kV > 200 V
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)	Level 1
Flammability Rating Oxygen Index: 28 to 34	UL 94 V–0 @ 0.125 in
Transistor Count	51
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test	•

1. For additional information, see Application Note <u>AND8003/D</u>.

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Units
V _{CC}	Positive Power Supply	GND = 0 V		7	V
V _{IN}	Input Voltage	GND = 0 V	GND = 0 V		V
l _{out}	Output Current	Continuous Surge		50 100	mA mA
T _A	Operating Temperature Range			-40 to +85	°C
T _{stg}	Storage Temperature Range			-65 to +150	°C
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	8 SOIC 8 SOIC	190 130	°C/W °C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	8 SOIC	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	8 TSSOP 8 TSSOP	185 140	°C/W °C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	8 TSSOP	41 to 44 ±5%	°C/W
T _{sol}	Wave Solder	<2 to 3 sec @ 248°C		265	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Table 4. 100ELT SERIES PECL DC CHARACTERISTICS V_{CC} = 5.0 V; GND = 0.0 V (Note 2)

		-40°C 25°C		85°C							
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{CC}	Power Supply Current			22			22			22	mA
V _{OH}	Output HIGH Voltage (Note 3)	3915	3995	4120	3975	4045	4120	3975	4050	4120	mV
V _{OL}	Output LOW Voltage (Note 3)	3170	3305	3445	3190	3295	3380	3190	3295	3380	mV

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

2. Output parameters vary 1:1 with V_{CC}. V_{CC} can vary \pm 0.25 V. 3. Outputs are terminated through a 50 Ω resistor to V_{CC} – 2.0 V.

Table 5. TTL INPUT DC CHARACTERISTICS V_{CC} = 4.75 V to 5.25 V; T_A = -40^{\circ}C to 85 $^{\circ}C$

Symbol	Characteristic	Condition	Min	Тур	Мах	Unit
Ι _{ΙΗ}	Input HIGH Current	$V_{IN} = 2.7 V;$ $V_{IN} = (V_{CC} - 0.025) V$			20	μΑ
I _{IHH}	Input HIGH Current	V _{IN} = 7.0 V			100	μΑ
Ι _{ΙL}	Input LOW Current	V _{IN} = 0.5 V; V _{IN} = (GND + 0.025) V			-0.6	mA
V _{IK}	Input Clamp Diode Voltage	I _{IN} = -18 mA			-1.2	V
V _{IH}	Input HIGH Voltage		2.0		V _{CC} – 0.025 V	V
V _{IL}	Input LOW Voltage		GND + 0.025 V		0.8	V

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

MC100ELT22

			−40°C		25°C		85°C				
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
f _{MAX}	Maximum Input Frequency					500					MHz
t _{PLH}	Propagation Delay (Note 4) 1.5 V to 50%	0.6		1.2	0.9	1.2	1.5	0.6		1.35	ns
t _{PHL}	Propagation Delay (Note 4) 1.5 V to 50%	0.4		1.0	0.5	0.8	1.1	0.7		1.30	ns
t _{skew}	Within-Device Skew (Note 5) Device-to-Device Skew (Note 6)		50 300	100 600		50 300	100 600		50 350	100 750	ps
t _{JITTER}	CLOCK Random Jitter (RMS)					0.5					ps
t _r /t _f	Output Rise/Fall Time (20-80%)	0.4		1.6	0.4		1.6	0.4		1.6	ns

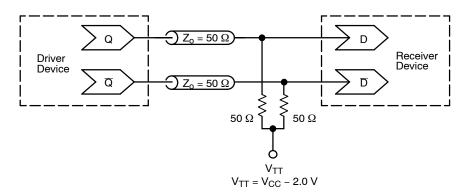
Table 6. AC CHARACTERISTICS V_{CC}= 4.75 V to 5.25 V; GND= 0.0 V

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

4. Specifications for standard TTL input signal.

5. Skew is measured between outputs under identical transitions and conditions on any one device.

6. Device-to-Device Skew for identical transitions at identical V_{CC} levels.





Resource Reference of Application Notes

- AN1405/D ECL Clock Distribution Techniques
- AN1406/D Designing with PECL (ECL at +5.0 V)
- AN1503/D ECLinPS™ I/O SPiCE Modeling Kit
- AN1504/D Metastability and the ECLinPS Family
- AN1568/D Interfacing Between LVDS and ECL
- AN1672/D The ECL Translator Guide
- AND8001/D Odd Number Counters Design
- AND8002/D Marking and Date Codes
- AND8020/D Termination of ECL Logic Devices
- AND8066/D Interfacing with ECLinPS
- AND8090/D AC Characteristics of ECL Devices

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*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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STYLE 1: PIN 1. EMITTER COLLECTOR 2. COLLECTOR 3. 4. EMITTER EMITTER 5. BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. DRAIN 8. STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: CATHODE 1 PIN 1. 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT 6. IOUT IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: PIN 1. GROUND BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE P-SOURCE 3 P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE 2. ANODE SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. CATHODE 8. STYLE 22 PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC COMMON CATHODE/VCC 3 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 COMMON ANODE/GND 8. STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4. SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5. 6.

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. 4. DRAIN, #2 GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 DRAIN 1 7. 8. **MIRROR 1** STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. LINE 1 OUT 8. STYLE 27: PIN 1. ILIMIT 2 OVI 0 UVLO З. 4. INPUT+ 5. SOURCE SOURCE 6. SOURCE 7. 8 DRAIN

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STYLE 4: ANODE ANODE PIN 1. 2. ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 BASE #2 3. COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. 4. GATE 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE 2. EMITTER 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE 6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF DASIC_SW_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK 8 VIN

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7.

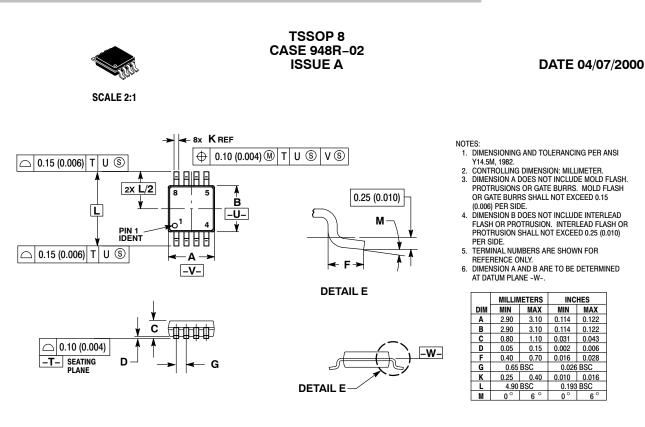
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